TOSHIBA Photocoupler GaAℓAs Ired & Photo−Diode Array

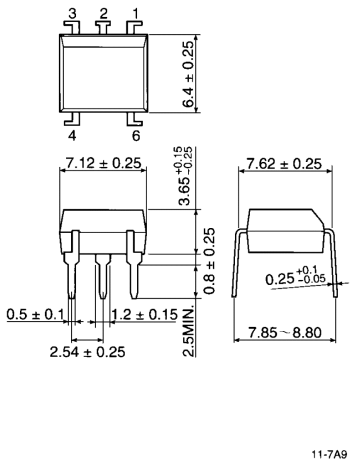
TLP591B

Telecommunication
Programmable Controllers
MOS Gate Driver
MOS FET Gate Driver

The TOSHIBA TLP591B consists of an aluminum galium arsenide infrared emitting diode optically coupled to a series connected photo−diode array in a six lead plastic DIP package.
TLP591B is suitable for MOS FET gate driver.
TLP591B has an internal shunt resistor to optimize switching speed.

- UL recognized: UL1577, file no. E67349

Unit in mm



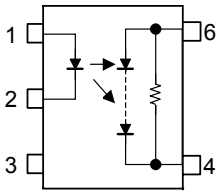
TOSHIBA 11−7A9

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	50	mA
	Forward current derating (Ta ≥ 25°C)	ΔI_F /°C	−0.5	mA /°C
	Pulse forward current (100μs pulse, 100pps)	I_{FP}	1	A
	Reverse voltage	V_R	3	V
	Junction temperature	T_j	125	°C
Detector	Forward current	I_{FD}	50	μA
	Reverse voltage	V_{RD}	10	V
	Junction temperature	T_j	125	°C
Storage temperature range		T_{stg}	−55~125	°C
Operating temperature range		T_{opr}	−40~85	°C
Lead soldering temperature (10 sec.)		T_{sol}	260	°C
Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note 1)		BV_S	2500	V_{rms}

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together, and pins 4 and 6 shorted together.

Pin Configuration (top view)



1. : Anode
2. : Cathode
3. : NC
4. : Cathode
6. : Anode

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward current	I_F	—	20	25	mA
Operating temperature	T_{opr}	−25	—	85	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	I_F = 10 mA	1.2	1.4	1.7	V
	Reverse current	I_R	V_R = 3 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	60	pF
Detector	Forward voltage	V_{FD}	I_{FD} = 10 μA	—	7	—	V
	Reverse current	I_{RD}	V_{RD} = 10 V	—	7	—	μA
	Capacitance (anode to cachode)	C_{TD}	V = 0, f = 1 MHz	—	—	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Open voltage	V_{OC}	I_F = 20 mA	7	8	—	V
Short Current	I_{SC}	I_F = 20 mA	24	40	—	μA

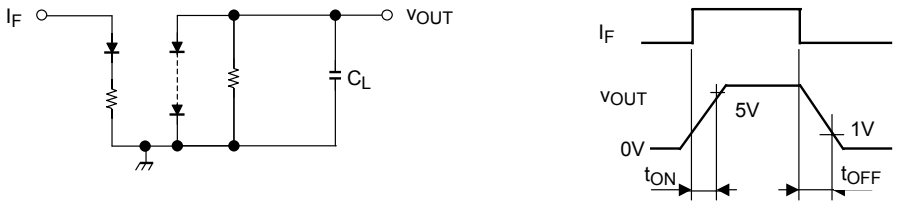
Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C_S	V_S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R_S	V_S = 500 V	5×10^{10}	10^{14}	—	
Isolation voltage	BV_S	AC, 1 minute	2500	—	—	Vrms
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	Vdc

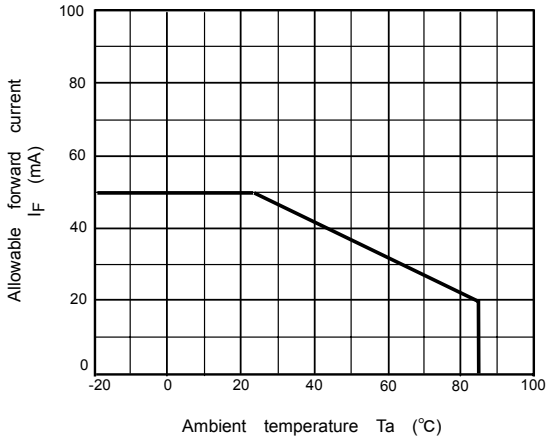
Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Turn−on time	t_{on}	I_F = 20 mA, C_L = 1000pF (Fig. 1)	—	0.2	—	ms
Turn−off time	t_{off}		—	3	—	ms

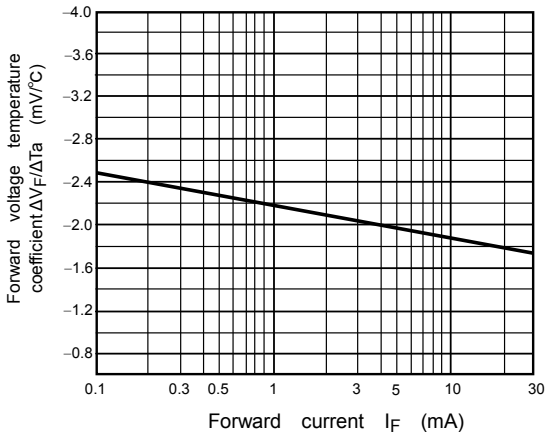
Fig. 1 Switching time test circuit



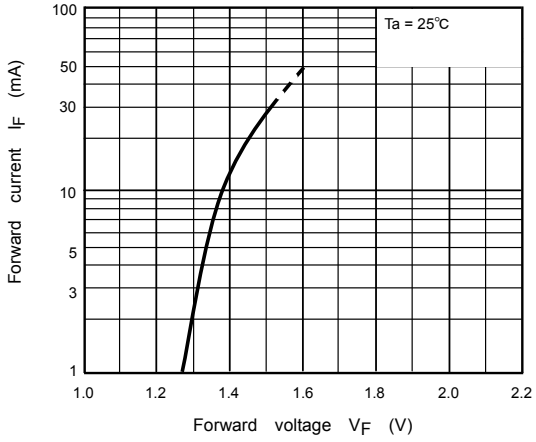
I_F – Ta



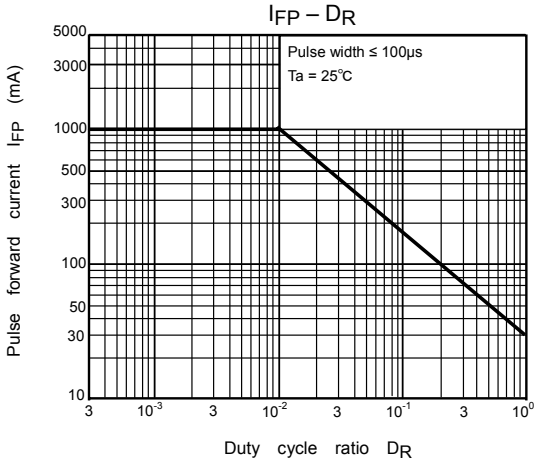
$\Delta V_F/\Delta Ta$ – I_F



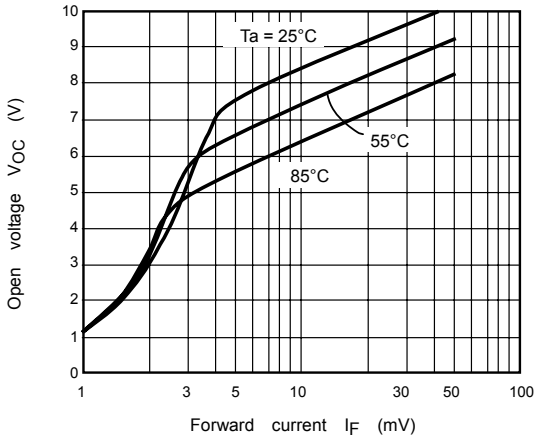
I_F – V_F



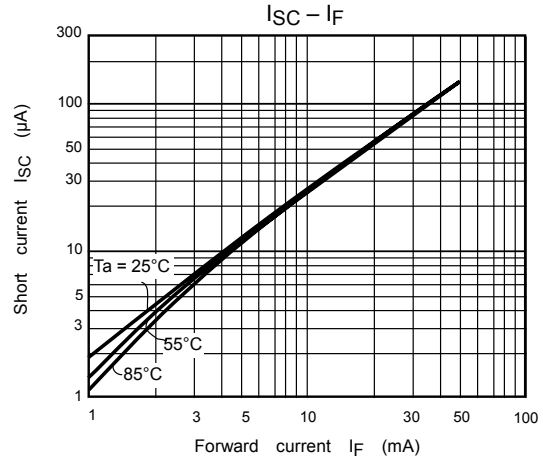
I_{FP} – D_R



V_{OC} – I_F



I_{SC} – I_F



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